Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2191	rsd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 15:24
S2	554	raised adj source/drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:46
S3	2710	S1 or S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:47
S4	0	recessed adj strained adj S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:47
S5	0	recessed adj strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:47
S6	70	strained and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:48
S7	59	cmos and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:53
S8	59	S7 and (@ad<"20040730" or @rlad<"20040730")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:11
S9	6	(("5155571") or ("5218213") or ("6358806") or ("6420218") or ("6504214") or ("6621131")).PN.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/09/16 09:54
S10	3	(("20010040292") or ("20010048119") or ("20030218212")).PN.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/09/16 09:54

S11	59	S8 not (S9 and S10)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:55
S12	47608	monolayer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:11
S13	497	S12 and SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:11
S14	106	S13 and sige	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:55
S15	3269	((257/347) or (438/300)).CCLS.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/09/16 15:55
S16	2716	(257/347).CCLS.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/09/16 15:55
S17	566	(438/300).CCLS.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/09/16 15:56
S18	550	S17 and (@ad<"20040730" or @rlad<"20040730")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:57
S19	47608	monolayer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:57
S20	8	S18 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:02
S21	0	S18 and api	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:02

S22	69	S18 and sige	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:06
S23	8408	((257/77,55,63,65,613,616,347) or (438/300,479,480,496,162,164,738, 740,970)).CCLS.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/09/27 13:09
S24	566	(438/300).CCLS.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/09/20 08:35
S25	47662	monolayer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 08:36
S26	388	S25 and sige	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 08:37
S27	43	S26 and epi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 08:44
S28	345	S26 not S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 08:44
S29	15	((silicon or si) with (oxygen or o) with (carbon or c) same (etchstop or (etch adj stop)) and (soi or (silicon adj on adj insulator)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 10:44
S30	2	((silicon or si) near (oxygen or o) with (carbon or c) same (etchstop or (etch adj stop)) and (soi or (silicon adj on adj insulator)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 10:23
S31	28286	(soi or (silicon adj on adj insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 10:44

S32	24772	((silicon adj germanium) or (sige) with (source or drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 15:36
S33	19180	etchstop or (etch adj stop)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 10:46
S34	595	S31 and S32 and S33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 10:46
S35	137	S34 and strain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 10:47
S36	3665	S31 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 15:36
S37	3058	S36 and (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 15:36
S38	551	S37 and raised	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:33
S39	177	S36 and ((raised adj source adj drain) or rsd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 15:38
S40	28349	(soi or (silicon adj on adj insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:33
S41	24832	((silicon adj germanium) or (sige) with (source or drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:33

S42	3681	S40 and S41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:33
S43	3071	S42 and (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:33
S44	552	S43 and raised	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:33
S45	177	S42 and ((raised adj source adj drain) or rsd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:33
S46	386	S44 not S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:34
S47	8442	((257/77,55,63,65,613,616,347) or (438/300,479,480,496,162,164,738,740,970)).CCLS.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2005/09/27 13:11
S48	2	S47 and ((silicon or si) with (oxygen or o) with (carbon or c)same (etchstop or (etch adj stop)) and (soi or (silicon adj on adj insulatior)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 13:16
S49	791	S47 and ((sicon adj germenium) or sige or (silocon adj germanium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 13:17
S52	0	(siocor(siliconadjoxideadjcarbide)or(siliconadjoxycarbide))and(etchstopo r(etchadjstop))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:50
S53	281	(sioc or(silicon adj oxide adj carbide)or(silicon adj oxycarbide))and(etchstopor(etch adj stop))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:51

S54	281	(sioc or (silicon adj oxide adj carbide) or (silicon adj oxycarbide)) and (etchstop or (etch adj stop))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:52
S55	132	(sige or (silicon adj germenium) or (silicon adj germanium)) and (sioc or (silicon adj oxide adj carbide) or (silicon adj oxycarbide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:59
S56	35	S55 and (etchstop or (etch adj stop))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:03
S57	126	S55 and (@ad<"20040730" or @rlad<"20040730")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:03
S58	34	S57 and (etchstop or (etch adj stop))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:03
S59	181	control$2 adj etch adj depth	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 08:19
S60	53	S59 and (etchstop or (etch adj stop))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 09:07
S61	38	S60 and (si or silicon or sige)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 09:08
S62	8170	soi and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 11:27
S63	6028	S62 and thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 11:28

S64	3331	S63 and nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 11:28
S65	3527	S63 and (nm or nanometer or (nano adj meter))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 11:28
S66	185084	S65 gate and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 11:29
S67	3118	S65 and gate and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 11:29
S68	2867	S67 and @ad<"20040730"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 11:30
S69	729	S68 and (soi with thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 11:31
S70	12	("20020142551" | "20030059995" | "20030189228" | "4616400" | "5814544" | "6063677" | "6225173" | "6391720" | "6406973" | "6465311" | "6509234" | "6583000").PN. OR ("6939751"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/06 11:57
S71	307	(soi with thickness)same cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 15:25